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1. General description

The TDA8025 is a cost-effective analog interface for asynchronous smart cards operating at 3 V, 1.8 V or optionally, 1.2 V. Using few external components, the TDA8025 provides integrated supply, protection and control functions for a range of applications.

2. Features

- Integrated circuit smart card interface
- 3 V, 1.8 V or 1.2 V smart card supply
- Low power consumption in inactive mode
- Three protected, half duplex, bidirectional buffered input/output lines (C4, C7 and C8)
- V_{CC} regulation:
 - ◆ 3 V, 1.8 V or optionally 1.2 V at ± 5 % using one 220 nF and one 470 nF low ESR multilayer ceramic capacitor.
 - \blacklozenge Current pulse handling for pulses of 40 nAs at V_{CC} = 3 V, 15 nAs at V_{CC} = 1.8 V or V_{CC} = 1.2 V up to 20 MHz
- Thermal and short-circuit protection for all card contacts
- Automatic activation and deactivation sequences triggered by short-circuit, card take-off, overheating, falling V_{DD(INTF)} and V_{DD(INTREGD)}
- Enhanced card-side ElectroStatic Discharge (ESD) protection of > 6 kV
- Clock signal using the internal oscillator or an external crystal (≤ 26 MHz) connected to pin XTAL1
- Card clock generation up to 20 MHz with synchronous frequency changes of f_{xtal}, ¹/₂ f_{xtal}, ¹/₄ f_{xtal} or ¹/₈ f_{xtal} using pins CLKDIV1 and CLKDIV2
- Non-inverted control of pin RST using pin RSTIN
- NDS certified
- Supply supervisors during power on and off:
 - V_{DD(INTREGD)} using a fixed threshold
 - ◆ V_{DD(INTF)} using resistor bridge threshold adjustment
- Built-in debouncing on card presence contacts (typically 4.5 ms)
- Multiplexed status signal using pin OFFN

3. Applications

- Pay TV
- Electronic payment
- Identification
- Bank card readers



4. Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Supplies							
V _{DDI(REG)}	regulator input	pin CONFIG = ground		3.6	5	5.5	V
	supply voltage	pin CONFIG = $V_{DDI(REG)}$; regulator is bypassed		3	3.3	3.6	V
V _{DD(INTF)}	interface supply	pin CONFIG = ground	<u>[1]</u>	1.6	3.0	3.3	V
	voltage	pin CONFIG = $V_{DDI(REG)}$ and $V_{DD(INTF)}$ not connected to $V_{DDI(REG)}$ and $V_{DD(INTREGD)}$		1.6	3.0	V _{DDI(REG)} + 0.3	V
		pin CONFIG = $V_{DDI(REG)}$ with $V_{DD(INTF)}$ connected to $V_{DDI(REG)}$ and $V_{DD(INTREGD)}$		3	3.3	3.6	V
I _{DDI(REG)}	regulator input	inactive mode					
	supply current	$V_{DDI(REG)} = 5 V; f_{xtal} = stopped$		-	-	300	μA
		$V_{DDI(REG)} = 5 \text{ V}; \text{ f}_{xtal} = 10 \text{ MHz};$ $f_{CLK} = \frac{1}{8} \text{ f}_{XTAL}$		-	-	2.5	mA
		active mode					
		$V_{CC} = 3 \text{ V}; \text{ I}_{CC} = 65 \text{ mA}$		-	-	85	mA
		$V_{CC} = 1.8 \text{ V}; I_{CC} = 65 \text{ mA}$		-	-	85	mA
		$V_{CC} = 1.2 \text{ V}; I_{CC} = 30 \text{ mA}$		-	-	50	mA
Card supp	ly voltage						
V _{CC}	supply voltage	including ripple					
		inactive mode					
		no load		-0.1	-	+0.1	V
		$I_{CC} = 1 \text{ mA}$		-0.1	-	+0.3	V
		active mode					
		3 V card:					
		I _{CC} < 65 mA DC		2.85	3.05	3.15	V
		single current pulse -100 mA; 2 μ s		2.76	3.05	3.20	V
		current pulses of 40 nAs at I _{CC} < 200 mA; t < 400 ns		2.76	3.05	3.20	V
		1.8 V card:					
		I _{CC} < 65 mA DC		1.71	1.83	1.89	V
		single current pulse -100 mA; 2 μ s		1.66	1.83	1.94	V
		current pulses of 15 nAs with I _{CC} < 200 mA; t < 400 ns		1.66	1.83	1.94	V
		1.2 V card:					
		I _{CC} < 30 mA DC		1.1	1.2	1.3	V
		single current pulse -100 mA; 2 μs		1.1	1.2	1.3	V
		current pulses of 15 nAs with I _{CC} < 200 mA; t < 400 ns		1.10	1.2	1.3	V
$V_{ripple(p-p)}$	peak-to-peak ripple voltage	pin V_{CC} ; 20 kHz to 200 MHz		-	-	350	mV

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Table 1.	Quick reference data	continued					
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Icc	supply current	0 V to 3 V		-	-	65	mA
		0 V to 1.8 V		-	-	65	mA
		0 V to 1.2 V		-	-	30	mA
SR	slew rate	up or down		0.02	0.14	0.26	V/μs
General							
t _{deact}	deactivation time	total sequence	[2]	35	80	100	μs
P _{tot}	total power dissipation	$T_{amb} = -25 \ ^{\circ}C \ to \ +85 \ ^{\circ}C$		-	-	0.56	W
T _{amb}	ambient temperatur	e		-25	-	+85	°C

[1] To enable the microcontroller to provide the required maximum voltage input level on XTAL1, $V_{DD(INTF)}$ must not exceed $V_{DD(INTREGD)} + 0.3$ V. See Section 8.1 on page 7 for specific limitations on the maximum $V_{DD(INTF)}$ voltage and Table 8 on page 23 for the limits of XTAL1.

[2] See Figure 12 on page 18.

5. Ordering information

Table 2.Ordering information

Type number	Package					
	Name	Description	Version			
TDA8025HN	HVQFN32	plastic thermal enhanced very thin quad flat package; no leads; 32 terminals; body $5 \times 5 \times 0.85$ mm	SOT617-1			

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6. Block diagram



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7. Pinning information

7.1 Pinning



7.2 Pin description

Table 3.	Pin des	scription	
Symbol	Pin	Type ^[1]	Description
CMDVCCN	J 1	I	microcontroller start activation sequence input; active LOW
TEST1	2	I	test pin; connect to GND
TEST2	3	I	test pin; connect to GND
$V_{\text{DD}(\text{INTF})}$	4	Р	interface supply voltage
CLKDIV2	5	I	sets the clock frequency; used together with pin CLKDIV1; see <u>Table 4 on page 12</u>
CLKDIV1	6	I	sets the clock frequency; used together pin CLKDIV2; see Table 4 on page 12 $\ensuremath{Page 12}$
VCC_SEL	17	I	optional 1.2 V selection control signal: active HIGH: $V_{CC} = 1.2 V$ active LOW: disables 1.2 V selection
VCC_SEL2	28	I	3 V or 1.8 V selection control signal: active LOW: V_{CC} = 3 V active HIGH: V_{CC} = 1.8 V when pin VCC_SEL1 is active LOW
PRESN	9	I	card presence contact input; active LOW ^[2]
PRES	10	I	card presence contact input; active HIGH ^[2]
I/O	11	I/O	card input/output data line (C7)
AUX2	12	I/O	card auxiliary 2 input/output data line (C8)[3]
AUX1	13	I/O	card auxiliary 1 input/output data line (C4)

Table 3.	Pin de	scription	continued
Symbol	Pin	Type <mark>[1]</mark>	Description
CGND	14	G	card signal ground
CLK	15	0	card clock (C3)
CONFIG	16	I	3.3 V or 5 V core regulator supply voltage selection; see Figure 3 on page 7
RST	17	0	card reset (C2)
V _{CC}	18	Ρ	card supply (C1); decouple to pin CGND using one 470 nF and one 220 nF capacitor with an Equivalent Series Resistance (ESR) < 100 m Ω
V _{DD(INTREGE}	₎ 19	Р	internally regulated supply voltage
GND	20	G	ground
$V_{\text{DDI}(\text{REG})}$	21	Р	regulator input supply voltage
RSTIN	22	I	microcontroller card reset input; active HIGH
OFFN	23	0	NMOS interrupt to microcontroller ^[4] ; active LOW; see <u>Section 8.10</u> on page 19
TEST3	24	0	test pin; do not connect to the application
PORADJ	25	I	power-on reset threshold adjustment input ^[4]
ENCLKIN	26	I	enable external clock on pin XTAL1; active HIGH
XTAL2	27	0	crystal connection pin; open when used with an external clock source
XTAL1	28	I	crystal connection pin; supply reference $V_{\text{DD}(\text{INTREGD})}$
			external clock input; supply reference V _{DD(INTF)}
I/OUC	29	I/O	microcontroller input/output data line ^[4]
AUX1UC	30	I/O	microcontroller auxiliary 1 input/output data line ^[4]
AUX2UC	31	I/O	microcontroller auxiliary 2 input/output data line ^[4]
TEST4	32		test pin; connect to GND

[1] I = input, O = output, I/O = input/output, G = ground and P = power supply.

[2] If pin PRESN or pin PRES is true, the card is considered to be present. During card insertion, debouncing can occur on these signals. To counter this, the TDA8025 has a built-in debouncing timer (typically 4.5 ms).

[3] Using the internal pull-up resistor connected to pin V_{CC} .

[4] Using the internal pull-up resistor connected to pin V_{DD(INTF)}.

8. Functional description

Remark: Throughout this document the ISO7816 terminology conventions have been adhered to and it is assumed that the reader is familiar with these.

8.1 Power supplies

Two supply selections can be made using pin CONFIG (see <u>Figure 3</u>) depending on the active state of the pin:

- pin CONFIG is LOW: supply is pin V_{DDI(REG)}. The voltage range of the pin is between 3.6 V and 5.5 V. The regulator output range is between 3 V and 3.6 V.
- pin CONFIG is HIGH: supply pins V_{DDI(REG)} and V_{DD(INTREGD)} are connected together to bypass the regulator. Pin V_{DDI(REG)} voltage is between 3 V and 3.6 V.

10 μF 10 μF V_{DDI(REG)} V_{DDI(REG)} ╢⊢ ╢ Ŧ 10 μF 100 nF 100 nF ╢─┼ ╢⊢ ÷ ╢⊢ ╊ GND GND CONFIG V_{DD}(INTREGD) CONFIG V_{DD}(INTREGD) 20 16 21 19 20 16 21 19 REGULATOR REGULATOR SUPPLY SUPPLY INTERNAL INTERNAL REFERENCE REFERENCE V_{CC} V<u>cc</u> 18 18 VOLTAGE VOLTAGE V_{CC} V_{CC} 470 nF 220 nF 470 nF 220 nl SENSE LOOP SENSE LOOP 14 CGND 14 CGND \mathcal{A} \mathcal{H} 001aai959 001aai960 $3.6 \text{ V} < \text{V}_{\text{DDI(REG)}} < 5.5 \text{ V}$ $3 V < V_{DD(INTREGD)} < 3.6 V$ Power strategy Fig 3.

Remark: V_{DD(INTF)} must not exceed V_{DD(INTREGD)} + 0.3 V.

The following examples illustrate the voltage restrictions for $V_{DD(INTF)}$.

- CONFIG pin driven to GND: when $V_{DD(INTREGD)}$ is generated by the internal regulator, $V_{DD(INTF)}$ must not exceed 3.3 V.
- CONFIG pin is driven by V_{DDI(REG)} without V_{DD(INTF)} tied to V_{DDI(REG)} while V_{DD(INTREGD)} is tied to V_{DDI(REG)}: V_{DD(INTF)} must not exceed V_{DDI(REG)} + 0.3 V.
- CONFIG pin is driven by V_{DDI(REG)} with V_{DD(INTF)} tied to both V_{DDI(REG)} and V_{DD(INTREGD}): there no are restrictions for V_{DD(INTF)}.

The TDA8025 is held in the reset state until $V_{DD(INTREGD)}$ reaches $V_{th} + V_{hys}$ and PORADJ $V_{th} + V_{hys}$ plus the $t_{w(POR)}$ delay. If the $V_{DD(INTREGD)}$ and PORADJ signals fall below V_{th} , an automatic contact deactivation is triggered.

All interface signals to the microcontroller are referenced to $V_{DD(INTF)}$. In addition, all card contacts remain inactive during power-up and power-down cycles.

After powering up the device, pin OFFN remains LOW until pins CMDVCCN and PRES are both HIGH or pin CMDVCCN is HIGH and pin PRESN is LOW. During power off, pin OFFN is driven LOW when $V_{DD(INTREGD)}$ is below the falling threshold voltage (V_{th}).

When pin CMDVCCN is HIGH, the internal oscillator frequency $(f_{osc(int)})$ is switched to Low frequency (inactive) mode to reduce power consumption.

8.2 Voltage supervisors

8.2.1 Block diagram



8.2.2 Description

The voltage supervisors provide both the Power-On Reset (POR) and supply drop-out detection functions. They control the internal regulated supply voltage ($V_{DD(INTREGD)}$) and the microcontroller interface supply voltage ($V_{DD(INTF)}$) to ensure problem-free operation of the TDA8025.

By monitoring both $V_{DD(INTREGD)}$ and $V_{DD(INTF)}$, the voltage supervisors ensure these voltages are high enough to ensure correct operation of the TDA8025 and flawless communication between it and the microcontroller. This information is combined and sent to the digital controller in order to reset the TDA8025.

An extension of the power-on reset pulse width of ± 8 ms (t_{w(POR)}) is used to maintain the TDA8025 in inactive mode after the supply voltage power on or off sequences (see Figure 5).



8.2.3 V_{DD(INTREGD)} voltage supervisor with pin PORADJ connected to V_{DD(INTF)}

The TDA8025 remains in inactive mode irrespective of the levels on the command lines when

- V_{DD(INTREGD)} is less than V_{th} + V_{hys} (on pin V_{DD(INTREGD)})
- Pin PORADJ (monitoring V_{DD(INTF)}) is less than V_{th} + V_{hys}

In both cases, this lasts for the duration of $t_{w(POR)}$ after $V_{DD(INTREGD)}$ (on pin $V_{DD(INTREGD)}$) and $V_{DD(INTF)}$ (on pin $V_{DD(INTF)}$) have reached a level higher than $V_{th} + V_{hys}$. Two threshold voltages (V_{th}) are set by the hardware as follows:

- V_{DD(INTREGD)} threshold voltage: is set to the minimum supply voltage (2.7 V) specified for the digital part of the TDA8025
- V_{DD(INTF)} threshold voltage: is set to 1.24 V; see <u>Table 8 on page 23</u> for detailed information.

8.2.4 V_{DD(INTF)} voltage supervisor with external divider on pin PORADJ

An external resistor bridge can be used to divide $V_{DD(INTF)}$ on pin PORADJ to adapt the detection threshold when monitoring the microcontroller interface supply voltage.

Connecting the external resistor bridge as illustrated in Figure 4 on page 8 (R1 connected to $V_{DD(INTF)}$ and R2 connected to GND) to pin PORADJ overrides the internal threshold voltage V_{th} on pin $V_{DD(INTF)}$.

The threshold voltage on pin $V_{DD(INTF)}$ is calculated as follows:

$$V_{th} \text{ on pin } V_{DD(INTF)} = V_{bg} \left(\frac{l+RI}{R2}\right)$$
(1)

where

• V_{bg} is the bandgap voltage

When the resistor bridge is not used, pin PORADJ must be connected to pin V_{DD(INTF)}.

8.2.4.1 R1 and R2 resistor value calculation

This section describes how to calculate the values for resistors R1 and R2, taking into account the IC detector threshold spread and the external resistance, while ensuring reliable activation.

If for example, the controller is supplied by a regulator at 3.3 V \pm 20 %. Activation can be triggered above V_{DD(INTF)} = 3.3 V – 20 % (in this example 2.64 V). This activation threshold is defined as V_{DD(INTF)actmin}; i.e. the minimum value of V_{DD(INTF)} above which activation can always be triggered.

In addition to this external input, activation is permitted provided all the following conditions are met (see <u>Table 8 on page 23</u>): card presence, IC temperature, $V_{DD(INTF)}$ and $V_{DD(INTREGD)}$ supplies, etc.

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The voltage on PORADJ (V_{PORADJ}) can be calculated as: $V_{PORADJ} = \alpha \times V_{DD(INTF)}$

where:

- V_{DD(INTF)} is the interface supply voltage
- ratio α

$$\alpha = \frac{1}{1 + \frac{R1}{R2}}$$
(2)

An activation can be triggered if

$$V_{DD(INTF)} \times \alpha > V_{th(max)} \Rightarrow V_{DD(INTF)} > \frac{V_{th(max)}}{\alpha}$$
 (3)

where

• V_{th(max)} is the maximum rising external threshold voltage

The resistance spread of R1 between a minimum value R1_{min} and a maximum value R1_{max} induces a spread of the ratio α . This is also true for R2. Based on this:

$$V_{DD(INTF)actmin} = \frac{V_{th(max)}}{\alpha_{min}}$$
(4)

where

$$\alpha_{min} = \frac{1}{1 + \frac{RI_{max}}{R2_{min}}}$$
(5)

If $\Delta R1$ is the maximum spread of R1 and $\Delta R2$ is the maximum spread of R2 then:

$$RI_{max} = RI_{nom} + \Delta RI = RI_{nom} \cdot \left(I + \frac{\Delta RI}{RI_{nom}}\right)$$
(6)

$$R2_{min} = R2_{nom} - \Delta R2 = R2_{nom} \cdot \left(I - \frac{\Delta R2}{R2_{nom}}\right)$$
(7)

$$\alpha_{min} = \frac{1}{\frac{RI_{nom} \cdot \left(1 + \frac{\Delta RI}{RI_{nom}}\right)}{1 + \frac{RI_{nom} \cdot \left(1 - \frac{\Delta R2}{R2_{nom}}\right)}} = \frac{1}{1 + \frac{RI_{nom} \cdot (1 + \beta)}{R2_{nom} \cdot (1 - \beta)}} = \frac{V_{th(max)}}{V_{DD(INTF)actimin}}$$
(8)

where

- where β is the accuracy ratio of R1 and R2 (R1 and R2 are considered to be of the same type).

Then

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$$\frac{RI_{nom}}{R2_{nom}} = \frac{(I-\beta)}{(I+\beta)} \cdot \left(\frac{V_{DD(INTF)actmin}}{V_{th(max)}} - I\right)$$
(9)

$$R2_{nom} = \frac{R_{sum}}{\left(1 + \frac{RI_{nom}}{R2_{nom}}\right)} = \frac{R_{sum}}{\left(1 + \frac{(1 - \beta)}{(1 + \beta)} \cdot \left(\frac{V_{DD(INTF)actmin}}{V_{th(max)}} - 1\right)\right)}$$
(10)

If we target 1 % accuracy resistors (β = 0.01) and R_{sum} = 100 k Ω ; V_{th(max)} = 1.33 V (see Table 8 on page 23) and V_{DD(INTF)actmin} = 2.64 V then

- R1_{nom} = 50.88 kΩ
- R2_{nom} = 49.12 kΩ

Deactivation always occurs when

$$V_{PORADJ} < V_{th(min)} \Rightarrow V_{DD(INTF)deactmax} = \frac{V_{th(min)}}{\alpha_{max}}$$
 (11)

where

- V_{th(min)} is the minimum falling external threshold voltage
- V_{DD(INTF)}deactmax is the maximum value of V_{DD(INTF)} below which deactivation always occurs
- α_{max}

$$\alpha_{max} = \frac{1}{1 + \frac{RI_{nom} \cdot (1 - \beta)}{R2_{nom} \cdot (1 + \beta)}} = \frac{V_{th(min)}}{V_{DD(INTF)deactmax}}$$
(12)

With the resulting values for R1_{nom}, R2_{nom} and β ; V_{th(min)} = 1.17 V (see <u>Table 8 on</u> page 23) then V_{DD(INTF)deactmax} is 2.28 V.

8.3 Clock circuits

The clock signal (pin CLK) to the card is either generated by the clock signal input on pin XTAL1 or from a crystal ($f_{xtal} \le 26$ MHz) connected between pins XTAL1 and XTAL2. The voltage level applied to pin ENCLKIN defines which clock signal is used. When pin ENCLKIN is HIGH, connect the external clock to pin XTAL1.

Driving pin ENCLKIN LOW causes the external crystal to generate frequency f_{xtal} . Using pins CLKDIV1 and CLKDIV2, the crystal frequency can be set to either f_{xtal} , $\frac{1}{2}$ f_{xtal} , $\frac{1}{4}$ f_{xtal} or $\frac{1}{8}$ f_{xtal} .

The frequency change is synchronous and as such during transition, no pulse is shorter than 45 % of the smallest period. In addition, only the first and last clock pulse around the change have the correct width. When dynamically changing the frequency, the modification is only effective after 10 periods of XTAL1.

The duty cycle on pin CLK should be between 45 % and 55 %. To ensure this, the following must be applied:

• when the CLK frequency is f_{xtal}:

If an external clock is connected to pin XTAL1, the duty cycle should be between 48 % and 52 % with an input signal period transition time of less than 5 %.

If a crystal is used to generate f_{xtal} , the duty cycle on pin CLK should be between 45 % and 55 % depending on the layout, crystal characteristics and frequency.

• when CLK frequency is either f_{xtal} , $\frac{1}{2} f_{xtal}$, $\frac{1}{4} f_{xtal}$ or $\frac{1}{8} f_{xtal}$:

The duty cycle is guaranteed between 45 % and 55 % of the period frequency divisions.

When a crystal is used, it runs when pin ENCLKIN is driven LOW.



The clock signal is applied to the card based on the activation sequence as shown on the timing diagrams; see <u>Figure 8 on page 15</u> to <u>Figure 13 on page 19</u>.

When the signal applied to XTAL1 is controlled by the microcontroller, the clock signal is sent to the card only after the activation sequence finishes.

Table 4.Clock configuration

Clock circuitry definition (pins CLKDIV1 and CLKDIV2 can be changed simultaneously; a >10 XTAL1 period delay is needed. The minimum duration of any CLK state is 10 XTAL1 periods).

CLKDIV1	CLKDIV2	CLK
0	0	$\frac{1}{8} f_{xtal}$
0	1	¹ / ₄ f _{xtal}
1	1	¹ / ₂ f _{xtal}
1	0	f _{xtal}

8.4 Input and output circuits

When pins I/O and I/OUC are driven HIGH using an 11 k Ω resistor between pins I/O and V_{CC} and/or between pins I/OUC and V_{DD(INTF)}, both lines enter the idle state. Pin I/O is referenced to V_{CC} and pin I/OUC to V_{DD(INTF)}, thus allowing operation at V_{CC} \neq V_{DD(INTF)}.

The first side on which a falling edge occurs becomes the master. An anti-latch circuit disables falling edge detection on the other line, making it the slave. After a time delay $t_{d(edge)}$, the NMOS transistor on the slave-side is turned on. It then sends logic 0 to the master-side. When the master returns logic 1, the PMOS transistor on the slave side is turned on during the time delay (t_{pu}). After this sequence, both the master and slave return to their idle states.

The active pull-up feature ensures fast LOW-to-HIGH transitions making the TDA8025 capable of delivering more than 1 mA, up to an output voltage of 0.9 V_{CC} , at a load of 80 pF. At the end of the active pull-up pulse, the output voltage is dependent on the internal pull-up resistor value and load current. The current sent to and received from the card's I/O lines is internally limited to 15 mA at a maximum frequency of 1 MHz.



8.5 Inactive mode

After a power-on reset, the circuit enters the inactive mode, ensuring only the minimum number of circuits are active while the TDA8025 waits for the microcontroller to start a session. The inactive mode conditions are as follows:

- all card contacts are inactive. The impedance between the contacts and GND is approximately 200 $\Omega.$
- pins I/OUC, AUX1UC and AUX2UC are high-impedance using the 11 k Ω pull-up resistor connected to $V_{DD(INTF)}$
- the voltage generators and crystal oscillator are stopped
- the voltage supervisor is active
- · the internal oscillator runs in low frequency mode

8.6 Activation sequence

After the power-on and internal pulse width delay, the microcontroller checks the presence of the card using signal OFFN.

- The card is present when pins OFFN and CMDVCCN are HIGH
- The card is not present when pin OFFN is LOW and pin CMDVCCN is HIGH

If the card is in the reader (either pin PRESN or pin PRES is true), the microcontroller can start a card session by pulling pin CMDVCCN LOW. When using an external crystal, the following sequence is applied (see Figure 8):

- 1. pin CMDVCCN is pulled LOW (t0)
- 2. the crystal oscillator is triggered
- 3. the internal oscillator changes to its high frequency (t1)
- 4. V_{CC} rises either from 0 V to 3 V or 1.8 V on a controlled slope (t2)
- 5. pins I/O, AUX1 and AUX2 which were pulled LOW are driven HIGH (t3)
- 6. the clock (pin CLK) is applied to the C3 contact (t4)
- 7. pin RST is enabled (t5)

Calculation of the time delays is as follows:

- t1 = t0 + 2.13 ms
- t2 = t1
- t3 = t1 + 5T/2
- t4 = driven by host controller; > t3 and < t5
- t5 = t1 + 11T/2

Remark: The value of period T is 64 times the period interval of the internal oscillator (i.e. $\pm 25 \ \mu s. \ t3$ is called $t_{d(start)}$ and t5 is called $t_{d(end)}$.

The clock is applied to the card in one of the following ways:

- using pin RSTIN: The clock (pin CLK) start-up can be selected at either t3 or t5 using pin RSTIN. When pin RSTIN is HIGH and pin CMDVCCN is LOW, setting pin RSTIN to LOW between delays t3 and t5 sends signal CLK. Pin RSTIN should be held LOW until after delay t5. After passing t5, pin RST is a copy of pin RSTIN and has no further effect on pin CLK. It enables the microcontroller to precisely choose the CLK start by counting clock cycles from the falling edge of the RSTIN signal.
- not using pin RSTIN: If this feature is not needed, set both pins CMDVCCN and RSTIN to LOW. The clock (pin CLK) will start at delay t3 (a minimum 200 ns after the input/output transition). After delay t5, pin RSTIN can be set HIGH to receive the card Answer To Request (ATR).

Remark: Do not perform activation with pin RSTIN permanently pulled HIGH.

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The following sequence occurs when using an external clock connected to pin XTAL1 (see Figure 10):

- 1. external clock (XTAL1) started by the microcontroller (t0)
- 2. CMDVCCN is pulled LOW and the internal oscillator changes to its high frequency (t1)
- 3. V_{CC} rises either from 0 V to 3 V or 0 V to 1.8 V on a controlled slope (t2)

- 4. pins I/O, AUX1 and AUX2 are enabled (t3)
- 5. CLK is applied to the C3 contact (t4)
- 6. pin RST is enabled (t5)

Calculation of the time delays is as follows:

- t1 = t0 + 2.13 ms
- $t2 = t1 = 3T/2 + 3(\frac{1}{fosc(int)low})$
- t3 = t1 + 5T/2
- t4 = driven by the host controller; > t3 and < t5
- t5 = t1 + 11T/2

Remark: The value of period T is 64 times the period interval of the internal oscillator (i.e. $\pm 25 \ \mu$ s). t3 is called t_{d(start)} and t5 is called t_{d(end)}. f_{osc(int)low} is the low (or inactive mode) frequency of the defined f_{osc(int)} parameter.

The CLK is applied to the card under control of pin RSTIN in exactly the same way as with the crystal oscillator.

Remark: Do not perform activation with pin RSTIN permanently pulled HIGH.



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8.7 Active mode

When the activation sequence has finished, the TDA8025 is in active mode. This mode enables data exchange between the card and the microcontroller using the input and output lines.

Depending on the layout and application test conditions, line C2 could become polluted with high frequency noise from line C3. For example, due to an additional 1 pF capacitance between lines C2/C3 and/or lines C2/C7. It is recommended that a 100 pF capacitor is added between line C2 and pin CGND, if this occurs.

When building the application, the following recommendations should be adhered to:

- Keep track C3 as far away as possible from other tracks.
- Keep the connection between pin CGND and line C5 straight. The two capacitors on line C1 should be connected to this ground track.
- Do not use ground loops between CGND and GND.

Following these layout recommendations will ensure that noise remains within the specifications and jitter on line C3 is less than 100 ps.

8.8 Deactivation sequence

When a session is completed, the microcontroller sets pin CMDVCCN to HIGH. The circuit then executes an automatic deactivation sequence by counting the sequencer back to the inactive state (see Figure 12 and Figure 13):

- 1. pin RST is pulled LOW (t11)
- 2. the clock is stopped, pin CLK is LOW (t12)
- 3. pins I/O, AUX1 and AUX2 are pulled LOW (t13)
- 4. V_{CC} falls to zero (t14). The deactivation sequence is completed when V_{CC} reaches its inactive state
- 5. all card contacts become low-impedance to GND. However, pins I/OUC, AUX1UC and AUX2UC remain pulled up to $V_{DD(INTREGD)}$ using the 11 k Ω resistor
- 6. The internal oscillator returns to its low frequency mode

Calculation of the time delays is as follows:

- t11 = t10 + 3T/64
- t12 = t11 + T/2
- t13 = t11 + T
- t14 = t11 + 3T/2

Remark: The value of period T is 64 times the period interval of the internal oscillator (i.e. $\pm 25 \ \mu s$).



TDA8025



8.9 V_{CC} regulator

Table 5. Selection of V_{CC} using pins VCC_SEL1 and VCC_SEL2

VCC_SEL1	VCC_SEL2	V _{CC}
0	0	3 V
0	1	1.8 V
1	0	1.2 V
1	1	1.2 V

The V_{CC} buffer is able to continuously deliver up to:

- 65 mA at 3 V
- 65 mA at 1.8 V
- 30 mA at 1.2 V

The V_{CC} buffer has an internal overload protection with a threshold value of \pm 135 mA. This detection is filtered, enabling spurious current pulses up to 200 mA with a duration of up to 200 ns to be drawn by the card without causing deactivation. However, the average current value must be below maximum.

To enhance V_{CC} stability, one 470 nF capacitor should be tied to pin CGND near pin 18 and one 220 nF capacitor should be tied to pin CGND near the C1 contact. Both capacitors should have an ESR < 100 m Ω .

8.10 Fault detection

The following conditions are monitored by the fault detection circuit:

- Short-circuit or high current on pin V_{CC}
- Card removal during transaction
- V_{DD(INTREGD)} falling

- V_{DD(INTF)} falling
- Overheating

Fault detection monitors two different situations (see Figure 15 on page 21):

- 1. Outside card sessions, pin CMDVCCN is HIGH: pin OFFN is LOW if the card is not in the reader and HIGH if the card is in the reader. Any supply voltage drop on $V_{DD(INTREGD)}$ or $V_{DD(INTF)}$ is detected by the supply supervisor. This generates an internal power-on reset pulse but does not act upon the pin OFFN signal. The card is not powered-up and as such short-circuits and overheating are not detected.
- 2. Within card sessions, pin CMDVCCN is LOW: when pin OFFN falls LOW, the fault detection circuit triggers the automatic emergency deactivation sequence (see Figure 14). When the system controller resets pin CMDVCCN to HIGH, after the deactivation sequence, pin OFFN is rechecked. If the card is still present, pin OFFN returns to HIGH. This check identifies the fault as either a hardware problem or a card removal incident.

On card insertion or removal, bouncing can occur in the PRES and/or PRESN signals. This depends on the type of card presence switch in the connector (normally open or normally closed) and the mechanical characteristics of the switch. To correct for this, a debouncing feature is integrated in to the TDA8025. This feature operates at a typical duration of $640 \times (\frac{1}{fosc(int)low})$. See Figure 15 for an overview of the debouncing feature.

Remark: $f_{osc(int)low}$ is the low frequency (or inactive) mode of the defined $f_{osc(int)}$ parameter.

On card insertion, pin OFFN goes HIGH after the debouncing time has elapsed. When the card is extracted, the automatic card deactivation sequence is performed on the first true or false transition on pin PRESN or pin PRES. After this pin OFFN goes LOW.





9. Limiting values

Remark: All card contacts are protected against any short-circuit to any other card contact. Stress beyond the levels indicated in <u>Table 6</u> can cause permanent damage to the device. This is a short-term stress rating only and under no circumstances implies functional operation under long-term stress conditions.

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DDI(REG)}	regulator input supply voltage		-0.3	+5.5	V
V _{DD(INTREGD)}	internal regulated supply voltage		-0.3	+5.5	V
Vı	input voltage	pins CMDVCCN, TEST1, TEST2, CLKDIV2, CLKDIV1, VCC_SEL1, VCC_SEL2, CONFIG, RSTIN, OFFN, TEST3, PORADJ, ENCLKIN, XTAL2, XTAL1, I/OUC, AUX1UC and AUX2UC	-0.3	+5.5	V
		card contact pins PRES, PRESN, I/O, RST, AUX1, AUX2 and CLK	-0.3	+6.5	V
T _{stg}	storage temperature		-55	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -25 \ ^{\circ}C \ to \ +85 \ ^{\circ}C$	-	0.56	W
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-25	+85	°C
V _{ESD}	electrostatic discharge voltage	pins I/O, RST, V _{CC} , AUX1, CLK, AUX2, PRES and PRESN; within typical application	-6	+6	kV
		Human Body Model (HBM); all pins; EIA/JESD22-A114-B, June 2000	-2	+2	kV
		Machine Model (MM); all pins; EIA/JESD22-A115-A, October 1997	-200	+200	V
		Charged Device Model (CDM);			
		all pins, except corner pins	-500	+500	V
		only corner pins (1, 8, 9, 16, 17, 24, 25 and 32)	-750	+750	V

10. Thermal characteristics

Table 7.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	with exposed pad soldered	42	K/W
		without exposed pad soldered	62	K/W

11. Characteristics

Table 8. Characteristics of IC supply voltage

 $T_{amb} = 25 \text{ °C}$; all parameters remain within limits but are only statistically tested for the temperature range; $f_{xtal} = 10 \text{ MHz}$; all currents flowing into the IC are positive; unless otherwise specified. Parameters specified as a function of $V_{DD(INTE)}$, $V_{DD(INTEG)}$, $V_{DD(INTEGD)}$ or V_{CC} refer to the actual value at the time of measurement.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Supply							
V _{DDI(REG)}	regulator input	pin CONFIG = ground		3.6	5	5.5	V
	supply voltage	pin CONFIG = $V_{DDI(REG)}$; regulator is bypassed		3	3.3	3.6	V
V _{DD} (INTREGD)	internal regulated supply voltage	pin CONFIG = ground	[1]	3	3.3	3.6	V
$V_{\text{DD}(\text{INTF})}$	interface supply	pin CONFIG = ground	[2]	1.6	3.0	3.3	V
	voltage	$ \begin{array}{l} \mbox{pin CONFIG} = V_{DDI(REG)} \\ \mbox{and } V_{DD(INTF)} \mbox{ not} \\ \mbox{connected to } V_{DDI(REG)} \\ \mbox{and } V_{DD(INTREGD)} \end{array} $		1.6	3.0	$V_{DDI(REG)} + 0.3$	V
		$\label{eq:point} \begin{array}{l} \text{pin CONFIG} = V_{DDI(REG)} \\ \text{with } V_{DD(INTF)} \text{ connected} \\ \text{to } V_{DDI(REG)} \text{ and} \\ V_{DD(INTREGD)} \end{array}$		3	3.3	3.6	V
I _{DDI(REG)}	regulator input supply current	inactive mode					
		$V_{DDI(REG)} = 5 V$ $f_{xtal} = stopped$		-	-	300	μA
		$\begin{split} V_{DDI(REG)} &= 5 \ V \\ f_{xtal} &= 10 \ MHz; \\ f_{CLK} &= \frac{1}{8} \ f_{xtal} \end{split}$		-	-	2.5	mA
		active mode					
		$V_{CC} = 3 V; I_{CC} = 65 mA$		-	-	85	mA
		$V_{CC} = 1.8 V;$ $I_{CC} = 65 mA$		-	-	85	mA
		$V_{CC} = 1.2 V;$ $I_{CC} = 30 mA$		-	-	50	mA
I _{DD(INTF)}	interface supply current			-	-	100	μA
V _{th}	threshold voltage	pin $V_{DD(INTREGD)}$; falling		2.60	2.70	2.80	V
		pin $V_{DD(INTREGD)}$; rising		2.65	2.80	2.95	V
		pin PORADJ; falling		1.17	1.24	1.31	V
		pin PORADJ; rising		1.19	1.26	1.33	V
V _{hys}	hysteresis voltage	pin $V_{DD(INTREGD)}$		50	100	150	mV
$t_{w(POR)}$	power-on reset pulse width			5	8	18	ms
$\Delta V_{th} / \Delta T$	threshold voltage variation with temperature			-	-	0.25	mV/°C

Table 8. Characteristics of IC supply voltage ...continued

 $T_{amb} = 25 \,^{\circ}C$; all parameters remain within limits but are only statistically tested for the temperature range; $f_{xtal} = 10 \,$ MHz; all currents flowing into the IC are positive; unless otherwise specified. Parameters specified as a function of $V_{DD(INTE)}$, $V_{DD(INTE)}$, $V_{DD(INTEG)}$, $V_{DD(INTEGD)}$ or V_{CC} refer to the actual value at the time of measurement.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
l.	leakage current	pin PORAD $I < 0.5 V$	_0 1	+4	+10	
·L	lounage our off	$\frac{1}{100} = \frac{1}{100} = \frac{1}$	_1	-	±1	μ. τ
Card supply	v voltage ^[3]		•			μι
Cdec	decoupling	connected to Vcc	550	_	830	nF
- 050	capacitance					•••
V _{CC}	supply voltage	including ripple				
		inactive mode				
		no load	-0.1	-	+0.1	V
		$I_{CC} = 1 \text{ mA}$	-0.1	-	+0.3	V
		active mode				
		3 V card:				
		I _{CC} < 65 mA DC	2.85	3.05	3.15	V
		single current pulse –100 mA; 2 μs	2.76	3.05	3.20	V
		current pulses of 40 nAs at I _{CC} < 200 mA; t < 400 ns	2.76	3.05	3.20	V
		1.8 V card:				
		I _{CC} < 65 mA DC	1.71	1.83	1.89	V
		single current pulse –100 mA; 2 μs	1.66	1.83	1.94	V
		current pulses of 15 nAs with I _{CC} < 200 mA; t < 400 ns	1.66	1.83	1.94	V
		1.2 V card:				
		I _{CC} < 30 mA DC	1.1	1.2	1.3	V
		single current pulse –100 mA; 2 μs	1.1	1.2	1.3	V
		current pulses of 15 nAs with I _{CC} < 200 mA; t < 400 ns	1.10	1.2	1.3	V
V _{ripple(p-p)}	peak-to-peak ripple voltage	pin V _{CC} ; 20 kHz to 200 MHz	-	-	350	mV
I _{CC}	supply current	0 V to 3 V	-	-	65	mA
		0 V to 1.8 V	-	-	65	mA
		0 V to 1.2 V	-	-	30	mA
SR	slew rate	up or down	0.02	0.14	0.26	V/µs
Crystal osci	illator: pins XTAL1	and XTAL2				
C _{ext}	external capacitance	pins XTAL1/XTAL2; depending on the crystal or resonator specification	-	-	15	pF

Table 8. Characteristics of IC supply voltage ...continued

 $T_{amb} = 25 \circ C$; all parameters remain within limits but are only statistically tested for the temperature range; $f_{xtal} = 10 \text{ MHz}$; all currents flowing into the IC are positive; unless otherwise specified. Parameters specified as a function of VDD(INTE), VDD(INTEGD) or VCC refer to the actual value at the time of measurement.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{xtal}	crystal frequency	card clock reference; crystal oscillator	2	-	26	MHz
f _{ext}	external frequency	external clock on pin XTAL1	0	-	26	MHz
V _{IL}	LOW-level input voltage	pin XTAL1	-0.3	-	$+0.3V_{DD(INTF)}$	V
V _{IH}	HIGH-level input voltage	pin XTAL1				
		$V_{DD(INTF)} \le V_{DD(INTREGD)}$	$0.7V_{DD(INTF)}$	-	$V_{DD(INTF)} + 0.3$	V
		V _{DD(INTF)} > V _{DD(INTREGD)}	$0.7V_{DD(INTF)}$	-	V _{DD(INTREGD)} + 0.3	V
Data lines:	pins I/O, I/OUC, AU	X1, AUX2, AUX1UC and AUX	2UC			
t _d	delay time	falling edge on pins I/O and I/OUC or vise versa	-	-	200	ns
t _{w(pu)}	pull-up pulse width		-	-	100	ns
f _{io}	input/output frequency	on data lines	-	-	1	MHz
Ci	input capacitance	on data lines	-	-	10	pF
Data lines t	o the card: pins I/O	, AUX1 and AUX2 ^[4]				
Vo	output voltage	inactive mode				
		no load	0	-	0.1	V
		l _o = 1 mA	-	-	0.3	V
l _o	output current	from data lines when in inactive mode with pins grounded	-	-	-1	mA
V _{OL}	LOW-level output voltage	I _{OL} = 1 mA	0	-	0.3	V
		$I_{OL} \ge 15 \text{ mA}$	$V_{CC}-0.4$	-	V _{CC}	V
V _{OH}	HIGH-level output voltage	no DC load	0.9V _{CC}	-	V _{CC} + 0.1	V
		I_{OH} < -40 μ A; 3 V	0.75V _{CC}	-	V _{CC} + 0.1	V
		l _{OH} < –20 μA; 1.8 V or 1.2 V card	0.75V _{CC}	-	V _{CC} + 0.1	V
		current limit $I_{OH} = -15 \text{ mA}$	0	-	0.4	V
V _{IL}	LOW-level input voltage	$V_{CC} = +3 V$	-0.3	-	+0.8	V
		$V_{CC} = +1.8 V$	-0.3	-	+0.6	V
		$V_{CC} = +1.2 V$	-0.3	-	+0.4	V
V _{IH}	HIGH-level input voltage		0.6V _{CC}	-	V _{CC} + 0.3	V
V _{hys}	hysteresis voltage	pin I/O	-	350	-	mV
I _{IL}	LOW-level input current	pin I/O; $V_{IL} = 0 V$	-	-	600	μA
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